

MDS12L THRU MDS110L

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MDS12L THRU MDS110L

1.0A Surface Mount Low VF Schottky Barrier Single-Phase Bridge Rectifiers-20-100V

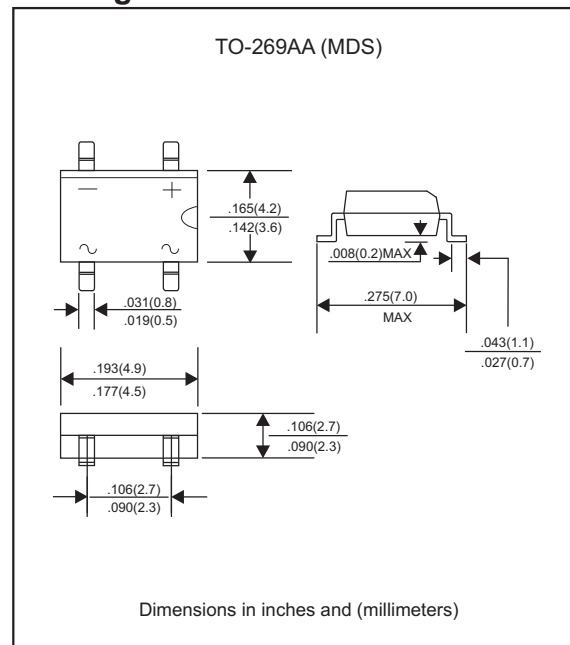
Features

- Schottky barrier chips in TO-269AA bridge.
- Metal semiconductor junction with guard ring.
- Silicon epitaxial planar chips.
- Very low forward drop down voltage.
- For use in low voltage, high efficiency inverters, free wheeling, and polarity protection applications.
- Lead-free parts meet RoHS requirements.
- Suffix "-H" indicates Halogen free parts, ex. MDS12L-H.

Mechanical data

- Epoxy:UL94-V0 rated flame retardant
- Case : Molded plastic, TO-269AA (MDS)
- Terminals : Solder plated, solderable per MIL-STD-750, Method 2026
- Polarity : marked on body
- Mounting Position : Any
- Weight : Approximated 0.11 gram

Package outline



Maximum ratings and Electrical Characteristics (AT $T_A=25^{\circ}\text{C}$ unless otherwise noted)

PARAMETER	CONDITIONS	Symbol	MIN.	TYP.	MAX.	UNIT
Average Forward rectified current	2.0x2.0" (5.0x5.0mm) copper pad, See Fig.1	$I_{F(AV)}$			1.0	A
Peak Forward surge current	8.3ms single half sine-wave (JEDEC methode)	I_{FSM}			30	A
Reverse current	$V_R = V_{RRM} \quad T_J = 25^{\circ}\text{C}$	I_R			0.5	mA
	$V_R = V_{RRM} \quad T_J = 100^{\circ}\text{C}$				20	
Thermal resistance	Junction to ambient	$R_{\theta JA}$		75		$^{\circ}\text{C/W}$
	Junction to lead	$R_{\theta JL}$		15		
Diode junction capacitance	f=1MHz and applied 4V DC reverse voltage	C_J		250		pF
Storage temperature		T_{STG}	-65		+175	$^{\circ}\text{C}$

SYMBOLS	V_{RRM}^{*1} (V)	V_{RMS}^{*2} (V)	V_R^{*3} (V)	V_F^{*4} (V)	Operating temperature T_J , (°C)
MDS12L	20	14	20	0.44	-55 to +125
MDS14L	40	28	40		
MDS16L	60	42	60	0.625	-55 to +150
MDS18L	80	56	80	0.75	
MDS110L	100	70	100		

*1 Repetitive peak reverse voltage

*2 RMS voltage

*3 Continuous reverse voltage

*4 Maximum forward voltage per element at 1.0A peak

Rating and characteristic curves (MDS12L THRU MDS110L)

Fig.1 - Forward Current Derating Curve

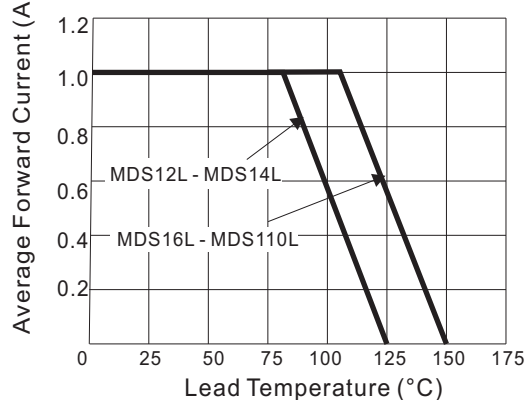


Fig. 2 - Maximum Non-Repetitive Peak Forward Surge Current

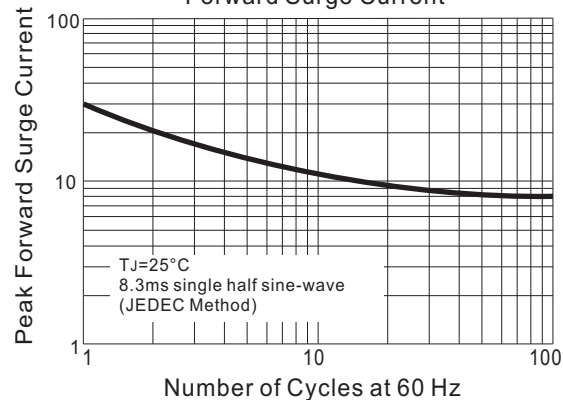


Fig. 3 - Typical Instantaneous Forward Characteristics

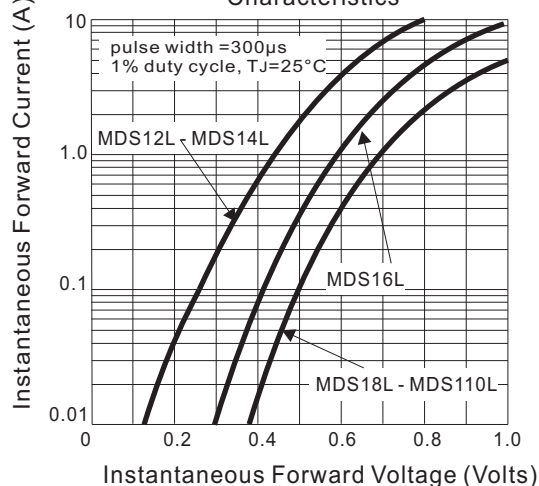


Fig. 4A - Typical Reverse Characteristics

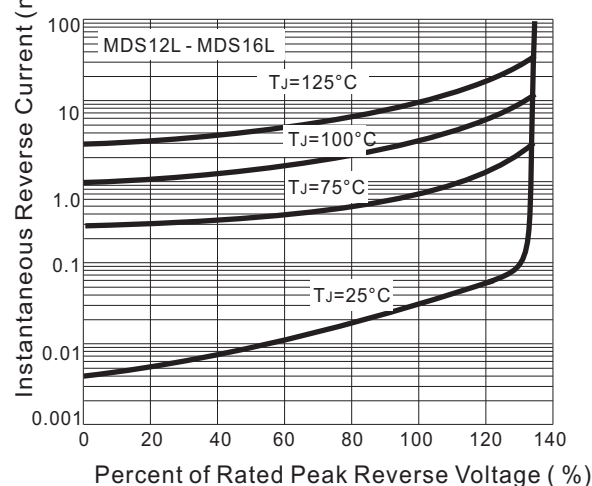


Fig. 5 - Typical Junction Capacitance

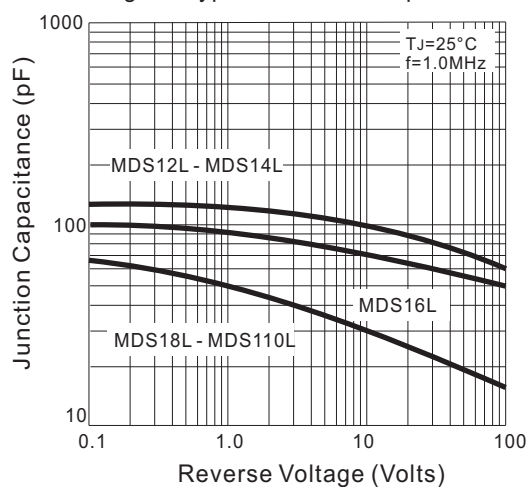
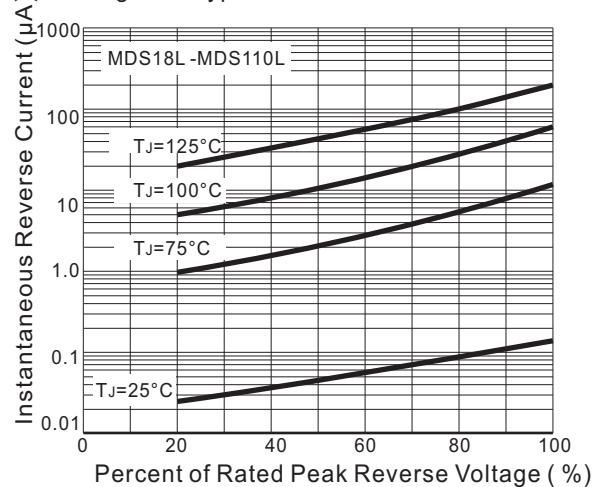
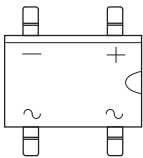
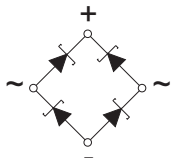


Fig. 4B - Typical Reverse Characteristic



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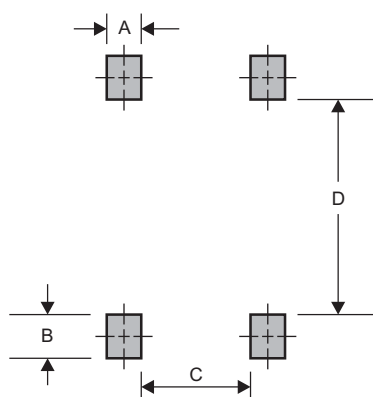
Pinning information

Simplified outline	Symbol
	

Marking

Type number	Marking code
MDS12L	MDS12L
MDS14L	MDS14L
MDS16L	MDS16L
MDS18L	MDS18L
MDS110L	MDS110L

Suggested solder pad layout

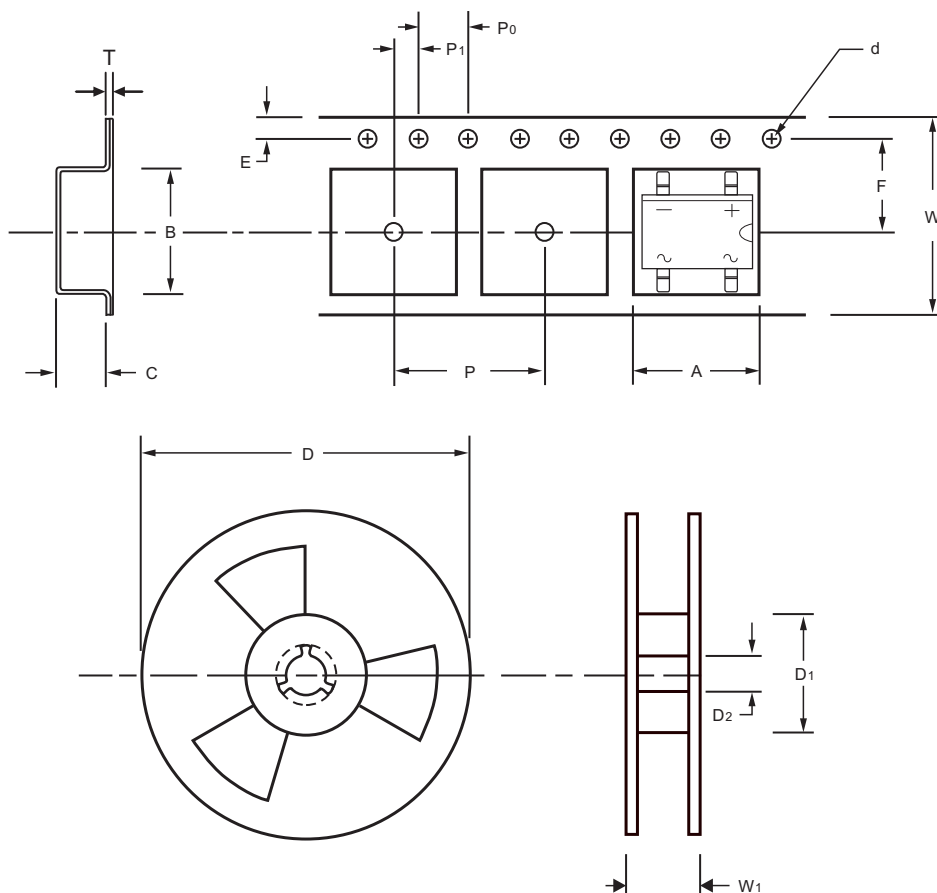


Dimensions in inches and (millimeters)

PACKAGE	A	B	C	D
TO-269AA (MDS)	0.023 (0.58)	0.030 (0.76)	0.070 (1.78)	0.226 (5.75)

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Packing information



unit:mm

Item	Symbol	Tolerance	TO-269AA (MDS)
Carrier width	A	0.1	5.00
Carrier length	B	0.1	7.24
Carrier depth	C	0.1	3.33
Sprocket hole	d	0.1	1.50
13" Reel outside diameter	D	2.0	330.00
13" Reel inner diameter	D1	min	50.00
7" Reel outside diameter	D	2.0	-
7" Reel inner diameter	D1	min	-
Feed hole diameter	D2	0.5	13.00
Sprocket hole position	E	0.1	1.75
Punch hole position	F	0.1	5.50
Punch hole pitch	P	0.1	8.00
Sprocket hole pitch	P0	0.1	4.00
Embossment center	P1	0.1	2.00
Overall tape thickness	T	0.1	0.30
Tape width	W	0.3	12.00
Reel width	W1	1.0	18.00

Note: Devices are packed in accordance with EIA standard RS-481-A and specifications listed above.

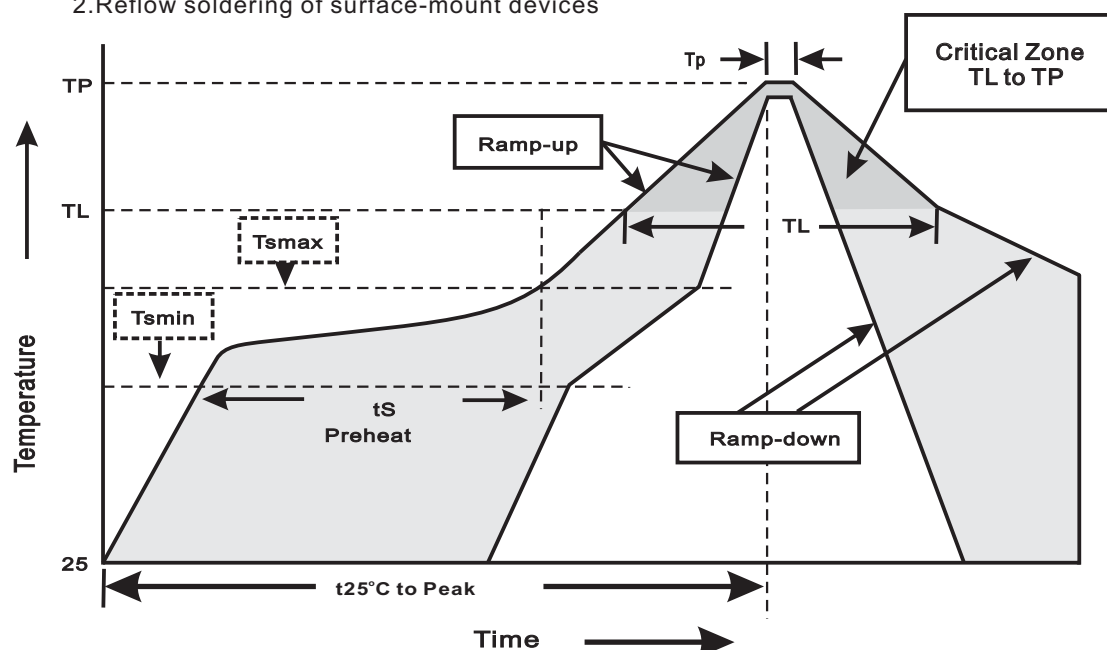
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Reel packing

PACKAGE	REEL SIZE	REEL (pcs)	COMPONENT SPACING (m/m)	BOX (pcs)	INNER BOX (m/m)	REEL DIA, (m/m)	CARTON SIZE (m/m)	CARTON (pcs)	APPROX. GROSS WEIGHT (kg)
TO-269AA (MDS)	13"	2,500	8.0	5,000	337*337*37	330	350*330*360	40,000	11.8

Suggested thermal profiles for soldering processes

- 1.Storage environment: Temperature=5°C~40°C Humidity=55%±25%
- 2.Reflow soldering of surface-mount devices



3.Reflow soldering

Profile Feature	Soldering Condition
Average ramp-up rate(T _L to T _P)	<3°C/sec
Preheat -Temperature Min(T _{smmin}) -Temperature Max(T _{smmax}) -Time(min to max)(t _s)	150°C 200°C 60~120sec
T _{smmax} to T _L -Ramp-upRate	<3°C/sec
Time maintained above: -Temperature(T _L) -Time(t _L)	217°C 60~260sec
Peak Temperature(T _P)	255°C-0/+5°C
Time within 5°C of actual Peak Temperature(t _P)	10~30sec
Ramp-down Rate	<6°C/sec
Time 25°C to Peak Temperature	<6minutes

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High reliability test capabilities

Item Test	Conditions	Reference
1. Solder Resistance	at $260\pm5^{\circ}\text{C}$ for $10\pm2\text{sec.}$ immerse body into solder $1/16''\pm1/32''$	MIL-STD-750D METHOD-2031
2. Solderability	at $245\pm5^{\circ}\text{C}$ for 5 sec.	MIL-STD-202F METHOD-208
3. High Temperature Reverse Bias	$V_R=80\%$ rate at $T_J=125^{\circ}\text{C}$ for 168 hrs.	MIL-STD-750D METHOD-1038
4. Forward Operation Life	Rated average rectifier current at $T_A=25^{\circ}\text{C}$ for 500hrs.	MIL-STD-750D METHOD-1027
5. Intermittent Operation Life	$T_A = 25^{\circ}\text{C}$, $I_F = I_O$ On state: power on for 5 min. off state: power off for 5 min. on and off for 500 cycles.	MIL-STD-750D METHOD-1036
6. Pressure Cooker	$15P_{SIG}$ at $T_A=121^{\circ}\text{C}$ for 4 hrs.	JESD22-A102
7. Temperature Cycling	-55°C to $+125^{\circ}\text{C}$ dwelled for 30 min. and transferred for 5min. total 10 cycles.	MIL-STD-750D METHOD-1051
8. Forward Surge	8.3ms single half sine-wave, one surge.	MIL-STD-750D METHOD-4066-2
9. Humidity	at $T_A=85^{\circ}\text{C}$, RH=85% for 1000hrs.	MIL-STD-750D METHOD-1021
10. High Temperature Storage Life	at 175°C for 1000 hrs.	MIL-STD-750D METHOD-1031